

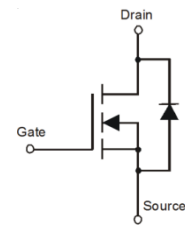
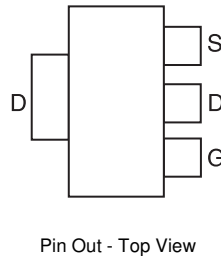
Product Summary

BV _{DSS}	R _{DS(on)} (Ω)	I _D (A)
60V	0.08 @ V _{GS} = 10V	5.3
	0.15 @ V _{GS} = 4.5V	2.8

Description and Applications

This MOSFET features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control



Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

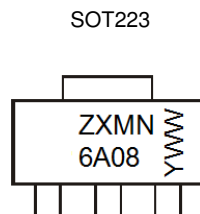
- Case: SOT223
- Case Material: Molded Plastic.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208 Ⓜ3
- Weight: 0.112 grams (Approximate)

Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A08GTA	ZXMN6A08	7	12	1,000
ZXMN6A08GTC	ZXMN6A08	13	12	4,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



ZXMN6A08 = Product Type Marking Code
 YWW = Date Code Marking
 Y or Y = Last Digit of Year (ex: 5 = 2015)
 WW or WW = Week Code (01 - 53)

Absolute Maximum Ratings

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	V_{GSS}	± 20	V	
Continuous Drain Current $V_{GS} = 10V$	I_D	$T_A = +25^\circ C$ (Note 6)	5.3	A
		$T_A = +70^\circ C$ (Note 6)	4.2	A
		$T_A = +25^\circ C$ (Note 5)	3.8	A
Pulsed Drain Current (Note 7)	I_{DM}	20	A	
Continuous Source Current (body diode)(Note 6)	I_S	2.1	A	
Pulsed Source Current (body diode)(Note 7)	I_{SM}	20	A	
Power Dissipation at $T_A = +25^\circ C$ (Note 5)	P_D	2	W	
Linear Derating Factor		16	mW/ $^\circ C$	
Power Dissipation at $T_A = +25^\circ C$ (Note 6)	P_D	3.9	W	
Linear Derating Factor		31	mW/ $^\circ C$	
Linear Derating Factor	T_J, T_{STG}	-55 to +150	$^\circ C$	

Thermal Characteristics (@ $T_A = +25^\circ C$, unless otherwise specified.)

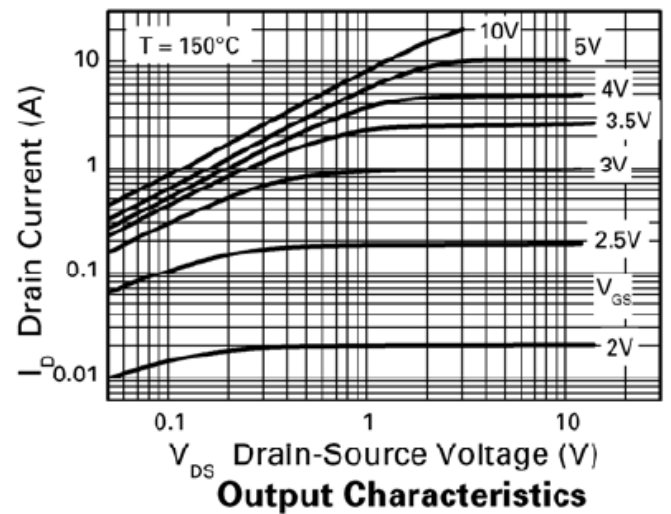
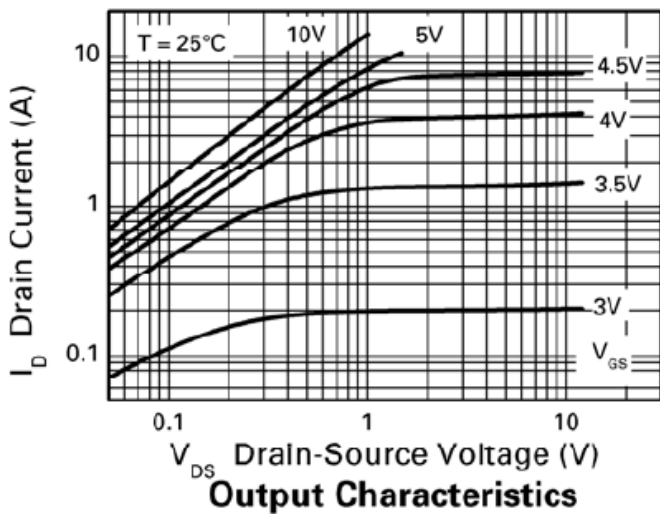
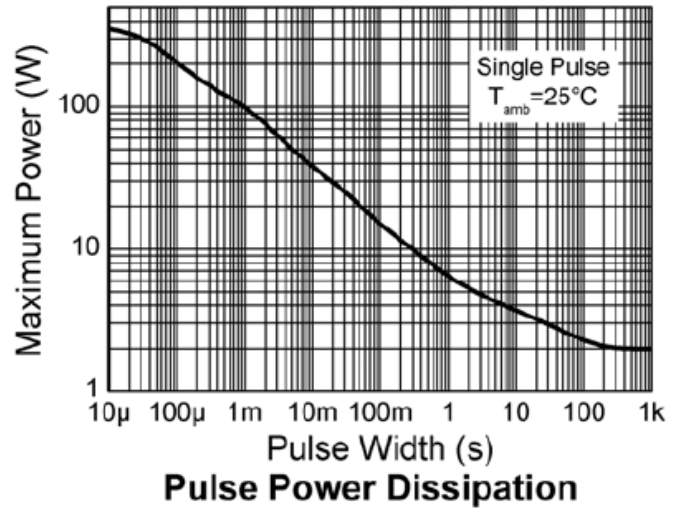
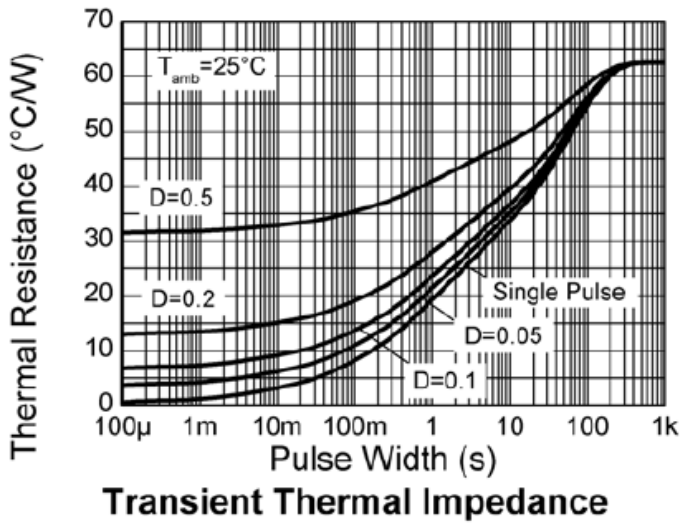
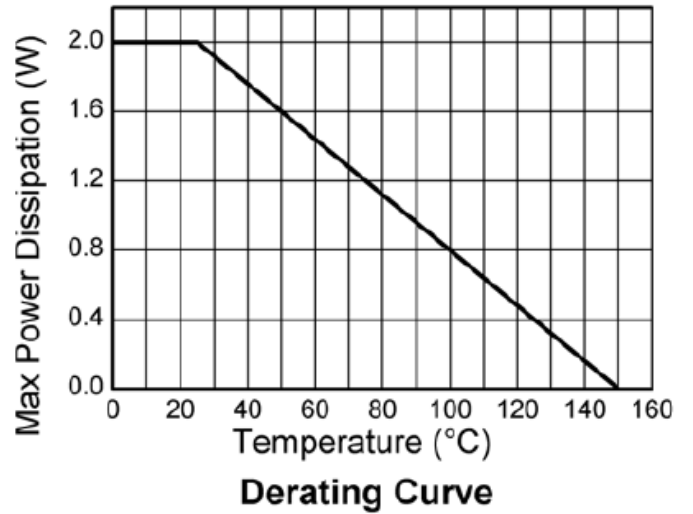
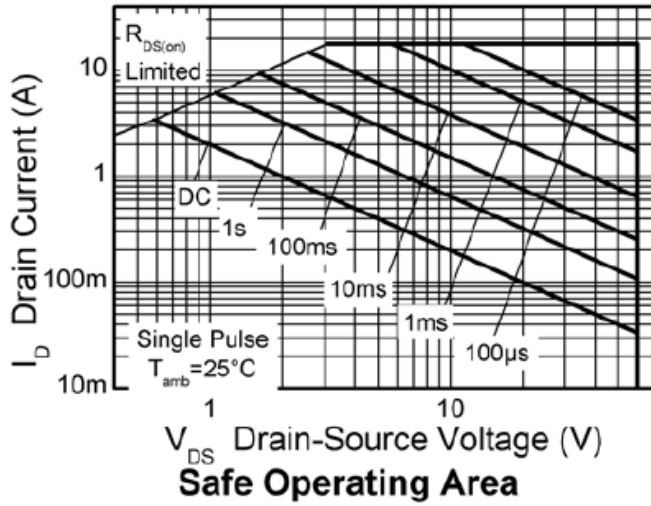
Characteristic	Symbol	Value	Units
Junction to Ambient (Note 5)	$R_{\theta JA}$	62.5	$^\circ C/W$
Junction to Ambient (Note 6)	$R_{\theta JA}$	32	$^\circ C/W$

Electrical Characteristics (@ $T_A = +25^\circ C$, unless otherwise specified.)

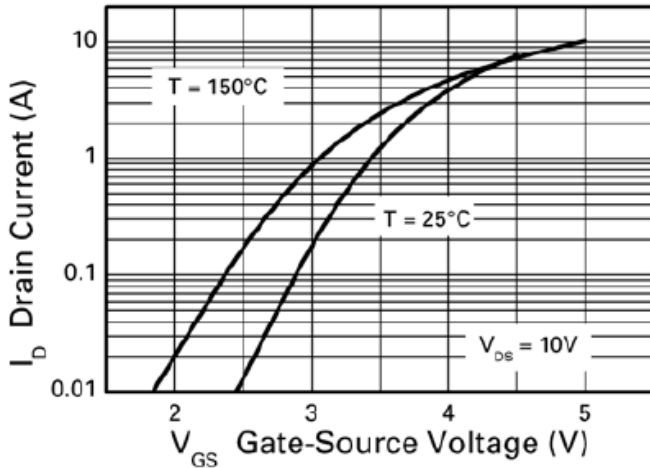
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	60	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	0.5	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	1	-	-	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-State Resistance (Note 8)	$R_{DS(on)}$	-	-	0.08	Ω	$V_{GS} = 10V, I_D = 4.8A$
		-	-	0.15	Ω	$V_{GS} = 4.5V, I_D = 4.2A$
Forward Transconductance (Notes 8 & 10)	g_{fs}	-	6.6	-	S	$V_{DS} = 15V, I_D = 4.8A$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	-	459	-	pF	$V_{DS} = 40V, V_{GS} = 0V,$ $f = 1MHz$
Output Capacitance	C_{oss}	-	44.2	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	24.1	-	pF	
Turn-On Delay Time (Note 9)	$t_{D(on)}$	-	2.6	-	ns	$V_{DD} = 30V, I_D = 1.5A$ $RG \approx 6.0\Omega, V_{GS} = 10V$
Turn-On Rise Time (Note 9)	t_r	-	2.1	-	ns	
Turn-Off Delay Time (Note 9)	$t_{D(off)}$	-	12.3	-	ns	
Turn-Off Fall Time (Note 9)	t_f	-	4.6	-	ns	
Gate Charge (Note 9)	Q_g	-	4.0	-	nC	$V_{DS} = 30V, V_{GS} = 5V$ $I_D = 1.4A$
Total Gate Charge (Note 9)	Q_g	-	5.8	-	nC	$V_{DS} = 30V, V_{GS} = 10V$ $I_D = 1.4A$
Gate-Source Charge (Note 9)	Q_{gs}	-	1.4	-	nC	
Gate Drain Charge (Note 9)	Q_{gd}	-	1.9	-	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (Note 8)	V_{SD}	-	0.88	1.2	V	$T_J = +25^\circ C, I_S = 4A,$ $V_{GS} = 0V$
Reverse Recovery Time (Note 10)	t_{rr}	-	19.2	-	ns	$T_J = +25^\circ C, I_S = 1.4A,$ $di/dt = 100A/\mu s$
Reverse Recovery Charge (Note 10)	Q_{rr}	-	30.3	-	nC	

- Notes:
5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 6. For a device surface mounted on FR4 PCB measured at $t \leq 10$ sec.
 7. Repetitive rating - 25mm x 25mm FR4 PCB, $D=0.02$, pulse width 300 μs - pulse width limited by maximum junction temperature.
 8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.
 9. Switching characteristics are independent of operating junction temperature.
 10. For design aid only, not subject to production testing.

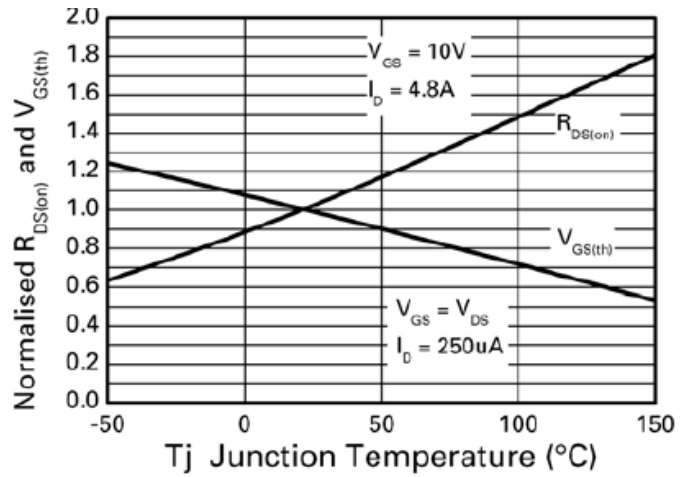
Typical Characteristics



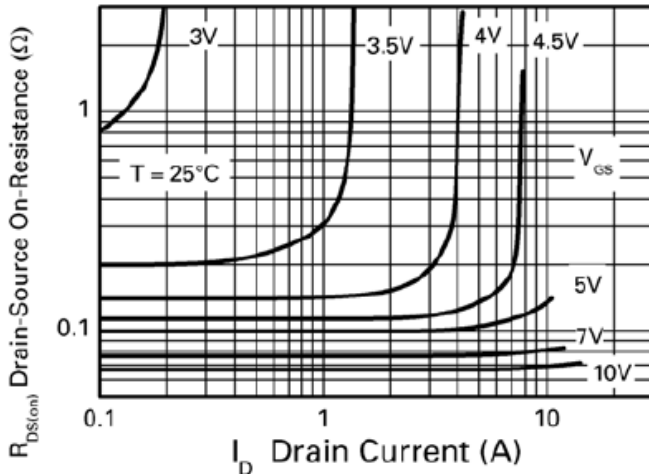
Typical Characteristics (continued)



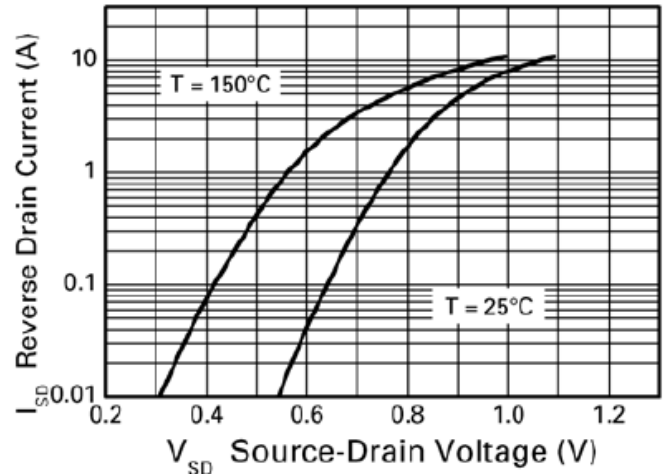
Typical Transfer Characteristics



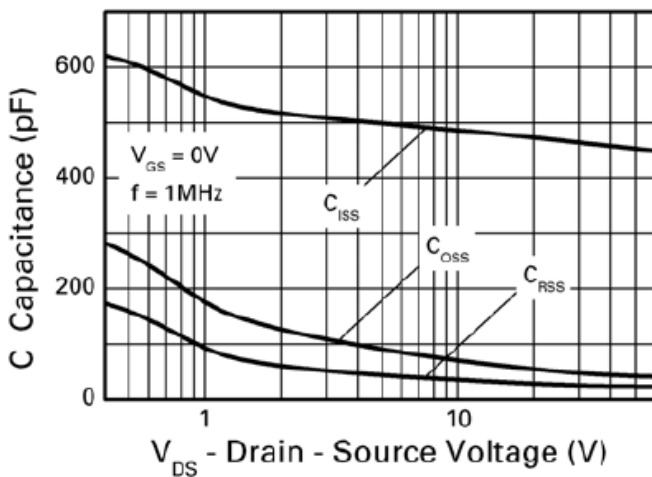
Normalised Curves v Temperature



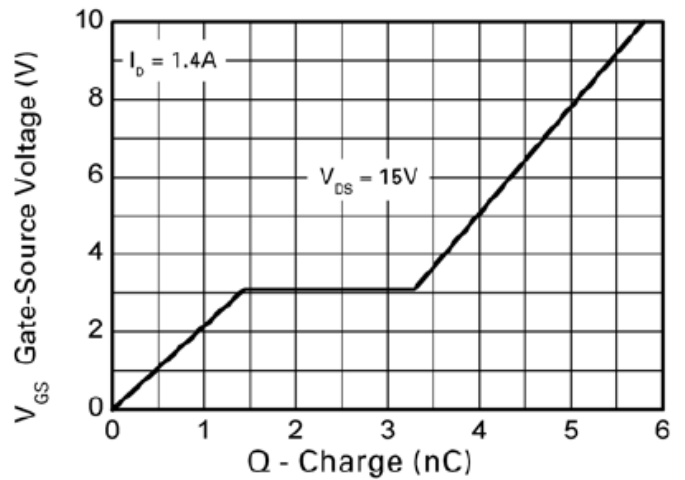
On-Resistance v Drain Current



Source-Drain Diode Forward Voltage

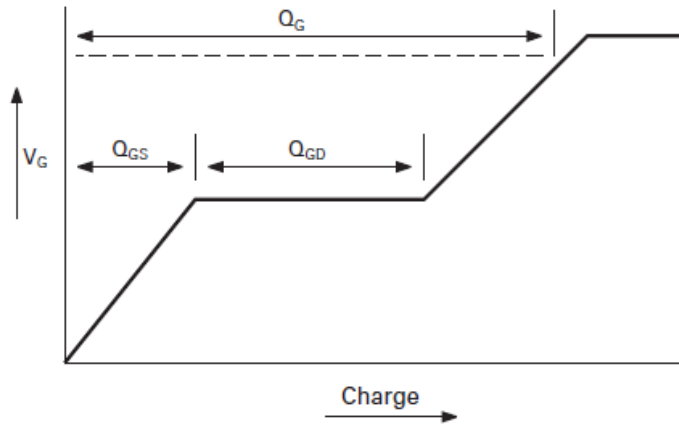


Capacitance v Drain-Source Voltage

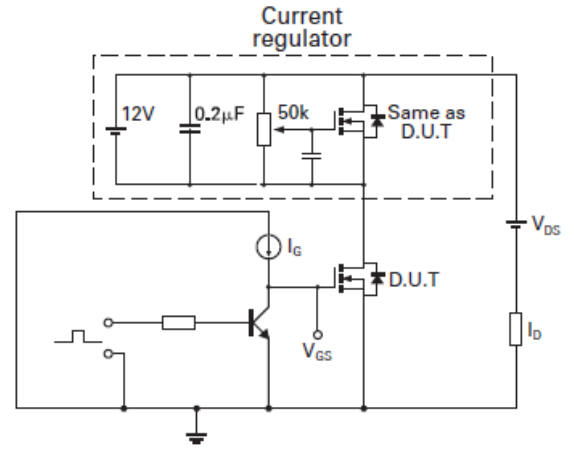


Gate-Source Voltage v Gate Charge

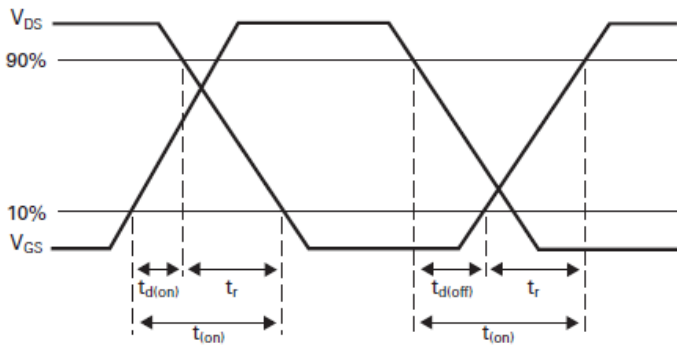
Test Circuits



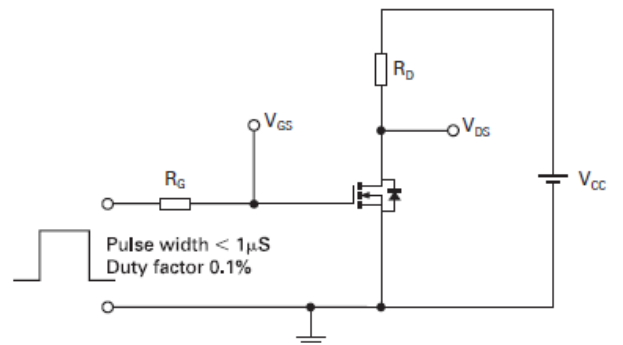
Basic gate charge waveform



Gate charge test circuit



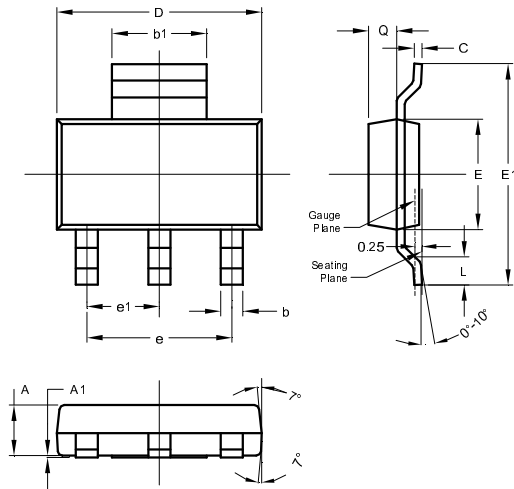
Switching time waveforms



Switching time test circuit

Package Outline Dimensions

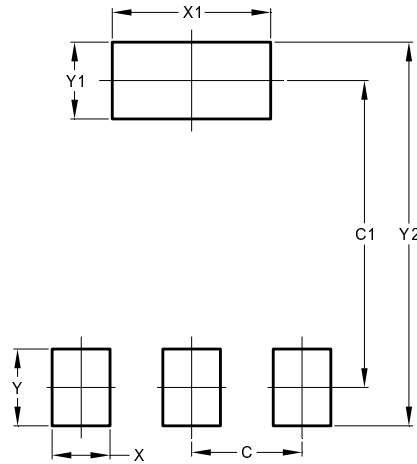
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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